

AMENDMENTS TO THE CLAIMS

1. (Previously Amended) A semiconductor device, comprising:
  - a contact plug including a tungsten film in an upper portion of the contact plug, formed on a semiconductor substrate;
  - a storage electrode including a tantalum nitride film formed on and contacting an upper surface of said tungsten film;
  - a capacitor dielectric film including a tantalum oxide film formed on and contacting an upper surface of said tantalum nitride film; and
  - a cell plate electrode including a tantalum nitride film formed on and contacting an upper surface of said tantalum oxide film, wherein the tantalum nitride films of said storage electrode and said cell plate electrode each have a work function greater than 4.95eV.
2. (Previously Amended) A semiconductor device, comprising:
  - a storage electrode including a first tantalum nitride film formed over a semiconductor substrate;
  - a capacitor dielectric film including a tantalum oxide film formed on and contacting an upper surface of said first tantalum nitride film; and
  - a cell plate electrode including a second tantalum nitride film formed on and contacting an upper surface of said tantalum oxide film and a copper film formed on and contacting an upper surface of said second tantalum nitride film, wherein said first and second tantalum nitride films each have a work function greater than 4.95eV.

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3. (Currently Amended) A semiconductor device, comprising:  
a semiconductor substrate;  
a contact plug including tungsten formed on the semiconductor substrate;  
a storage electrode including a first indium oxide film formed on and contacting an upper surface of said contact plug;  
a capacitor dielectric film including a tantalum oxide film formed on and contacting an upper surface of said first indium oxide film, wherein said tantalum oxide film consists of tantalum and oxygen; and  
a cell plate electrode including a second indium oxide film formed on and contacting an upper surface of said tantalum oxide film.

4. (Currently Amended) ~~The~~ A semiconductor device, comprising: according to claim 3  
a semiconductor substrate;  
a contact plug including tungsten formed on the semiconductor substrate;  
a storage electrode including a first indium oxide film formed on and contacting an upper surface of said contact plug;  
a capacitor dielectric film including a tantalum oxide film formed on and contacting an upper surface of said first indium oxide film; and  
a cell plate electrode including a second indium oxide film formed on and contacting an upper surface of said tantalum oxide film, wherein  
said storage electrode further includes a tantalum nitride film formed beneath and contacting a lower surface of said first indium oxide film.

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5. (Currently Amended) ~~The~~ A semiconductor device, comprising: according to claim 3  
a semiconductor substrate;  
a contact plug including tungsten formed on the semiconductor substrate;  
a storage electrode including a first indium oxide film formed on and contacting an upper  
surface of said contact plug;  
a capacitor dielectric film including a tantalum oxide film formed on and contacting an  
upper surface of said first indium oxide film; and  
a cell plate electrode including a second indium oxide film formed on and contacting an  
upper surface of said tantalum oxide film, wherein said cell plate electrode further includes a  
copper film formed on said second indium oxide film.

~~6. (Previously Amended) The semiconductor device according to claim 5, wherein said cell plate electrode further includes a tantalum nitride film formed between said second indium oxide film and said copper film, contacting both said second indium oxide film and said copper film.~~

~~7. (Previously Added) The semiconductor device according to claim 1, wherein said work function of the tantalum nitride films is up to 5.41eV.~~

~~8. (Previously Added) The semiconductor device according to claim 1, wherein said work function of the tantalum nitride films is equal to or greater than 5.41eV.~~

9. (Previously Added) The semiconductor device according to claim 1, wherein said work function of the tantalum nitride films is 5.41eV.

10. (Previously Added) The semiconductor device according to claim 2, wherein said work function of the tantalum nitride films is up to 5.41eV.

11. (Previously Added) The semiconductor device according to claim 2, wherein said work function of the tantalum nitride films is equal to or greater than 5.41eV.

12. (Previously Added) The semiconductor device according to claim 2, wherein said work function of the tantalum nitride films is 5.41eV.

D<sup>5</sup> 13. (New) The semiconductor device according to claim 1, wherein the bottom of said contact plug is formed with a conductor different from tungsten.

14. (New) The semiconductor device according to claim 3, wherein said tantalum oxide film consists of Ta<sub>2</sub>O<sub>5</sub>.

15. (New) A semiconductor device, comprising:  
a storage electrode including a tantalum nitride film formed above a semiconductor substrate;  
a capacitor dielectric film including a tantalum oxide film formed on and contacting an upper surface of said tantalum nitride film; and

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cont.  
a cell plate electrode including a tantalum nitride film formed on and contacting an upper surface of said tantalum oxide film, wherein the tantalum nitride films of said storage electrode and said cell plate electrode each have a work function greater than 4.95eV.

16. (New) A semiconductor device, comprising:

a storage electrode including a first indium oxide film formed above a semiconductor substrate;

a capacitor dielectric film including a tantalum oxide film formed on and contacting an upper surface of said first indium oxide film, wherein said tantalum oxide film consists of tantalum and oxygen; and

a cell plate electrode including a second indium oxide film formed on and contacting an upper surface of said tantalum oxide film.